



**CHENMKO ENTERPRISE CO.,LTD**

**CHTA64ZPT**

**SURFACE MOUNT  
PNP SILICON Transistor**

VOLTAGE 30 Volts CURRENT 1 Ampere

Lead free devices

**APPLICATION**

- \* Telephony and professional communication equipment.
- \* Other switching applications.

**FEATURE**

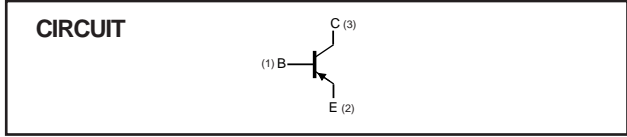
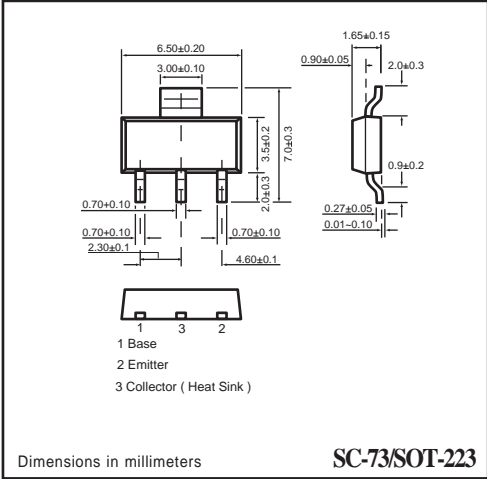
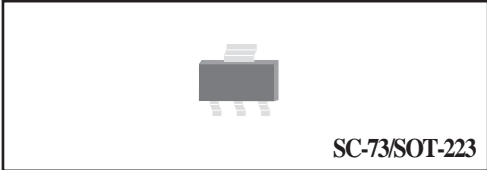
- \* Small flat package. ( SC-73/SOT-223 )
- \* Suitable for high packing density.

**CONSTRUCTION**

\*PNP SILICON Transistor

**MARKING**

\* ZGP



**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-10	V
I <sub>C</sub>	collector current (DC)		-	-1000	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	2	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

## RATING CHARACTERISTIC CURVES ( CHTA64ZPT )

### THEMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	357	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$V_{CB} = -30\text{ V}$	–	-100	nA
$I_{EBO}$	emitter cut-off current	$V_{EB} = -10\text{ V}$	–	-100	nA
$h_{FE}$	DC current gain	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V}$ $I_C = -100\text{ mA}; V_{CE} = -5\text{ V}$	10000 20000	–	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -100\text{ mA}; I_B = -0.1\text{ mA}$	–	-1.5	V
$V_{BE(ON)}$	base-emitter saturation voltage	$I_C = -100\text{ mA}; V_{CE} = 5\text{ V}$	–	-2	V
$f_T$	transition frequency	$I_C = -10\text{ mA}; V_{CE} = 5\text{ V};$ $f = 100\text{ MHz}$	125	–	MHz